

## Switch-mode Power Rectifier

60 V, 30 A

# MBR30L60CTG, MBRF30L60CTG

#### **Features and Benefits**

- Low Forward Voltage
- Low Power Loss/High Efficiency
- High Surge Capability
- 30 A Total (15 A Per Diode Leg)
- Guard-Ring for Stress Protection
- These Devices are Pb-Free and are RoHS Compliant

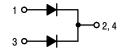
#### **Applications**

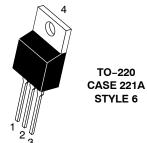
- Power Supply Output Rectification
- · Power Management
- Instrumentation

#### **Mechanical Characteristics:**

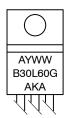
- Case: Epoxy, Molded
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Weight (Approximately): 1.9 Grams (TO-220 & TO-220FP)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds

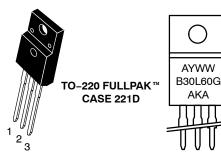
# SCHOTTKY BARRIER RECTIFIER 30 AMPERES, 60 VOLTS











A = Assembly Location

Y = Year

WW = Work Week

B30L60 = Device Code

G = Pb-Free Device

AKA = Polarity Designator

#### **ORDERING INFORMATION**

See detailed ordering and shipping information on page 2 of this data sheet.

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#### MAXIMUM RATINGS (Per Diode Leg)

Rating	Symbol	Value	Unit	
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage		V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	60	V
	(Per Leg) (Per Device) (Per Device)	I <sub>F(AV)</sub>	15 30	А
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)		I <sub>FSM</sub>	240	Α
Operating Junction Temperature (Note 1)		$T_J$	-55 to +150	°C
Storage Temperature		T <sub>stg</sub>	-65 to +175	°C
ESD Ratings: Machine Human Body	Model = C Model = 3B		> 400 > 8000	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Maximum Thermal Resistance MBR30L60CTG  MBRF30L60CTG  MBRF30L60CTG  Junction-to-Case Junction-to-Case Junction-to-Case Junction-to-Ambient	R <sub>θ</sub> JC R <sub>θ</sub> JA R <sub>θ</sub> JC R <sub>θ</sub> JA	2.1 70 5.0 75	°C/W

#### **ELECTRICAL CHARACTERISTICS** (Per Diode Leg)

Characteristic	Symbol	Тур	Max	Unit
$\label{eq:maximum Instantaneous Forward Voltage (Note 2)} \begin{array}{c} \text{(I}_F = 15 \text{ A, T}_C = 25^\circ\text{C)} \\ \text{(I}_F = 15 \text{ A, T}_C = 125^\circ\text{C)} \\ \text{(I}_F = 30 \text{ A, T}_C = 25^\circ\text{C)} \\ \text{(I}_F = 30 \text{ A, T}_C = 125^\circ\text{C)} \\ \end{array}$	VF	0.57 0.53 0.75 0.70	0.62 0.57 0.81 0.73	V
Maximum Instantaneous Reverse Current (Note 2) (Rated DC Voltage, $T_C$ = 25°C) (Rated DC Voltage, $T_C$ = 125°C)	İR	137 62	350 110	μA mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%.

#### **DEVICE ORDERING INFORMATION**

Device Order Number	Package Type	Shipping
MBR30L60CTG	TO-220 (Pb-Free)	50 Units / Rail
MBRF30L60CTG	TO-220FP (Pb-Free)	50 Units / Rail

<sup>1.</sup> The heat generated must be less than the thermal conductivity from Junction-to-Ambient:  $dP_D/dT_J < 1/R_{\theta JA}$ .

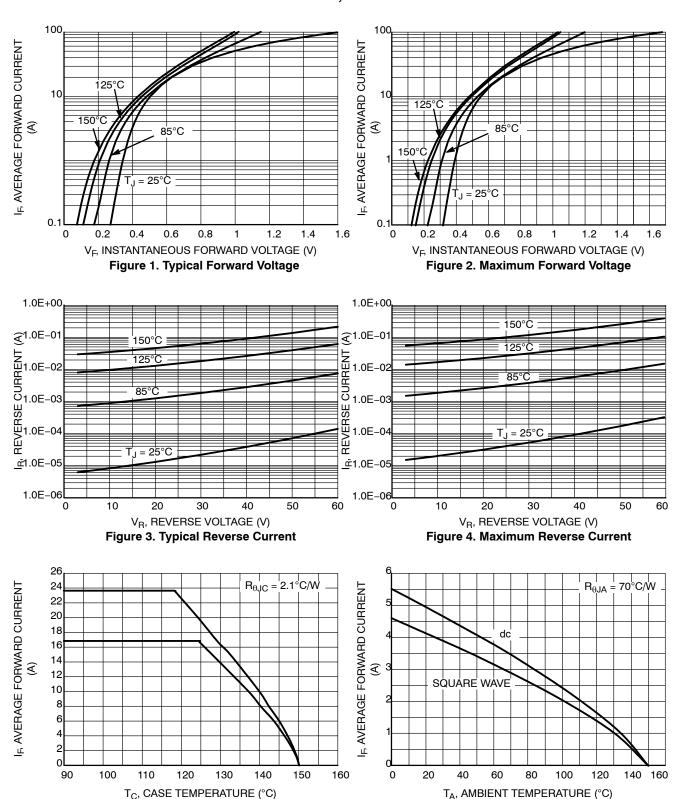


Figure 5. Current Derating, Case per Leg MBR30L60CT

Figure 6. Current Derating, Ambient per Leg MBR30L60CT

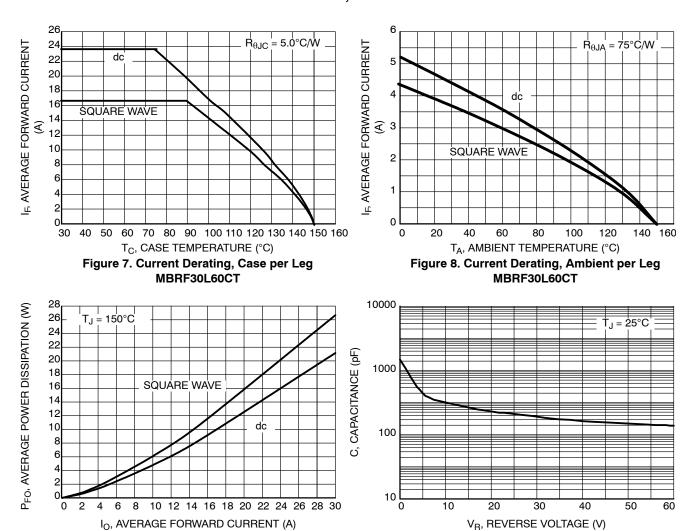


Figure 9. Forward Power Dissipation

Figure 10. Capacitance

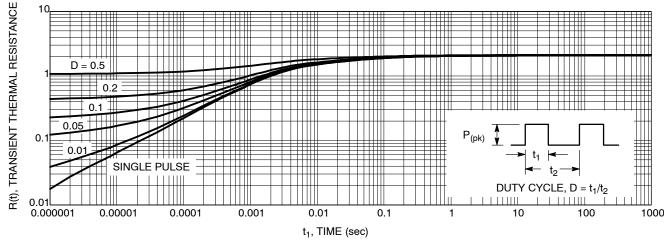


Figure 11. Thermal Response Junction-to-Case, per Leg for MBR30L60CT

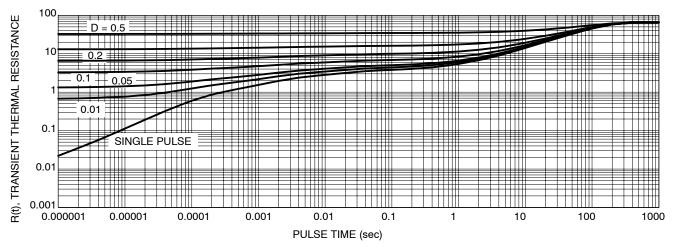


Figure 12. Thermal Response Junction-to-Ambient, per Leg for MBR30L60CT

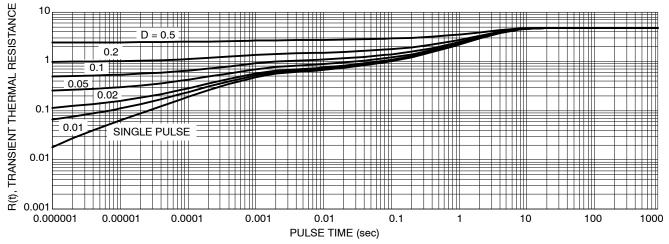


Figure 13. Thermal Response Junction-to-Case, per Leg for MBRF30L60CT

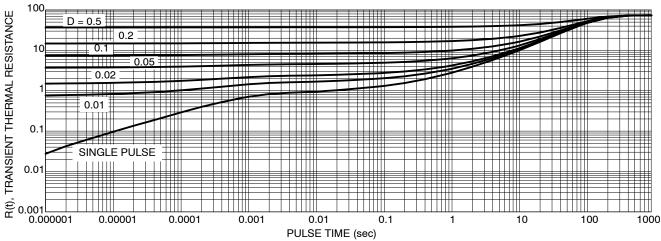
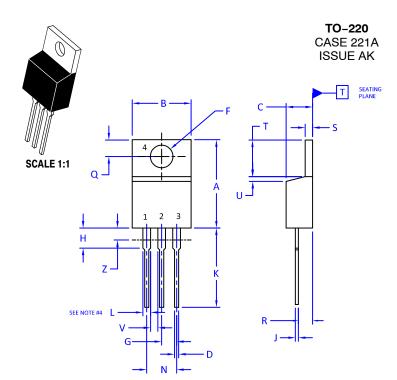


Figure 14. Thermal Response Junction-to-Ambient, per Leg for MBRF30L60CT

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**DATE 13 JAN 2022** 

#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 2009.
- 2. CONTROLLING DIMENSION: INCHES
- 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

#### 4. MAX WIDTH FOR F102 DEVICE = 1.35MM

	INCHES		MILLIMI	ETERS
DIM	MIN.	MAX.	MIN.	MAX.
Α	0.570	0.620	14.48	15.75
В	0.380	0.415	9.66	10.53
С	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.60	4.09
G	0.095	0.105	2.42	2.66
Н	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
К	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.41
Т	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045		1.15	
Z		0.080		2.04

STYLE 1: PIN 1. 2. 3. 4.	COLLECTOR EMITTER	STYLE 2: PIN 1. 2. 3. 4.	COLLECTOR	STYLE 3: PIN 1. 2. 3. 4.	ANODE	2. 3.	MAIN TERMINAL 1 MAIN TERMINAL 2 GATE MAIN TERMINAL 2
STYLE 5: PIN 1. 2. 3. 4.	DRAIN SOURCE	STYLE 6: PIN 1. 2. 3. 4.	CATHODE ANODE	STYLE 7: PIN 1. 2. 3. 4.	ANODE	2. 3.	CATHODE ANODE EXTERNAL TRIP/DELAY ANODE
STYLE 9: PIN 1. 2. 3. 4.			GATE SOURCE DRAIN SOURCE	STYLE 11: PIN 1. 2. 3. 4.		STYLE 12: PIN 1. 2. 3. 4.	MAIN TERMINAL 1 MAIN TERMINAL 2 GATE NOT CONNECTED

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### **MECHANICAL CASE OUTLINE**





SCALE 1:1

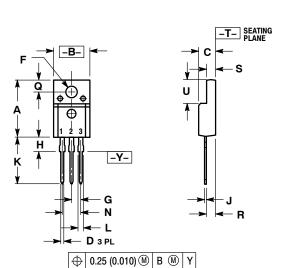
#### TO-220 FULLPAK CASE 221D-03 ISSUE K

**DATE 27 FEB 2009** 



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH
- 221D-01 THRU 221D-02 OBSOLETE, NEW STANDARD 221D-03.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.617	0.635	15.67	16.12
В	0.392	0.419	9.96	10.63
C	0.177	0.193	4.50	4.90
D	0.024	0.039	0.60	1.00
F	0.116	0.129	2.95	3.28
G	0.100 BSC		2.54 BSC	
Н	0.118	0.135	3.00	3.43
J	0.018	0.025	0.45	0.63
K	0.503	0.541	12.78	13.73
L	0.048	0.058	1.23	1.47
N	0.200	BSC	5.08	BSC
Q	0.122	0.138	3.10	3.50
R	0.099	0.117	2.51	2.96
S	0.092	0.113	2.34	2.87
U	0.239	0.271	6.06	6.88



#### **MARKING DIAGRAMS**

STYLE 1: PIN 1. GATE 2. DRAIN 3. SOURCE

STYLE 4: PIN 1. CATHODE

3. CATHODE

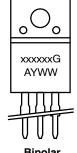
ANODE

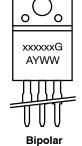
STYLE 2: PIN 1. BASE 2. COLLECTOR 3. EMITTER 2.

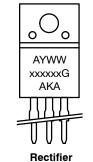
STYLE 6: PIN 1. MT 1 2. MT 2 3. GATE STYLE 5: PIN 1. CATHODE 2. ANODE 3. GATE

STYLE 3: PIN 1. ANODE

CATHODE
 ANODE







= Assembly Location xxxxxx = Specific Device Code G = Pb-Free Package Υ = Year

= Assembly Location WW = Work Week = Year XXXXXX = Device Code = Work Week = Pb-Free Package WW G AKA = Polarity Designator

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